| Form 1449 (Modified) | Atty Docket No. | Application No.: |
|---|---|---|
| | NOVLP098 | 10/800,409 |
| **Inf rmation Disclosure Statement By Applicant** | Applicant: Wu et al. | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | 03-11-2004 | 1762 |

**U.S. Patent Documents**

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|---|---|---|---|---|---|---|---|
| BC | A1 | 6,797,643 B2 | 09.2004 | Rocha-Alvarez et al. | | | |
| | A2 | 6,815,373 B2 | 11.2004 | Singh et al. | | | |
| | A3 | 6,914,014 B2 | 07.2005 | Li et al. | | | |
| | A4 | 2004/0101633 A1 | 05.2004 | Zheng et al. | | | |
| | A5 | 6,258,735 B1 | 07.2001 | Xia et al. | | | |
| | A6 | 6,715,498 B1 | 04.2004 | Humayun et al. | | | |
| | A7 | 5,849,640 | 12.1998 | Hsia et al. | | | |
| | A8 | 6,573,030 B1 | 06.03.03 | Fairbairn et al. | | | |
| | A9 | 2004/0096586 A1 | 05.2004 | Schulberg et al. | | | |
| | A10 | 2003/0198895 A1 | 10.2003 | Toma et al. | | | |
| BC | A11 | 6,846,380 B2 | 01.2005 | Dickinson et al. | | | |

**Foreign Patent or Published Foreign Patent Application**

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation Yes | Translation No |
|---|---|---|---|---|---|---|---|---|
| | | | | | | | | |

**Other Documents**

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|---|---|---|
| BC | C1 | U.S. Office Action mailed December 27, 2005, from U.S Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-002919]. |
| | C2 | U.S. Office Action mailed February 7, 2006, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821]. |
| | C3 | U.S. Office Action mailed December 20, 2005, from U.S Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820]. |
| | C4 | U.S. Office Action mailed December 20, 2005, from U.S Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867]. |
| | C5 | U.S. Office Action mailed January 9, 2006, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875]. |
| | C6 | U.S. Office Action mailed February 28, 2006, from U.S Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794]. |
| BC | C7 | Subramonium et al., "Pulsed PECVD Method for Modulating Hydrogen Content in Hard Mask", U.S. Application No. 11/318,269, filed December 23, 2005 (Atty Dkt: NOVLP144/NVLS-3102) |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (M dified) | Atty Docket No. | Application No.: |
|---|---|---|
| | NOVLP098 | 10/800,409 |
| **Information Disclosure Statement By Applicant** | Applicant: Wu et al. | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | 03-11-2004 | 1762 |

**U.S. Patent Documents**

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|---|---|---|---|---|---|---|---|
| BC | A | 6,340,628 | 1/22/02 | Van Cleemput, et al. | 438 | 586 | 12/12/00 |
| | B | 6,383,955 | 5/7/02 | Matsuki, et al. | 438 | 790 | 6/7/99 |
| BC | C | | | | | | |
| | D | | | | | | |
| | E | | | | | | |
| | F | | | | | | |
| | G | | | | | | |
| | H | | | | | | |
| | I | | | | | | |

**Foreign Patent or Published Foreign Patent Application**

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation Yes | Translation No |
|---|---|---|---|---|---|---|---|---|
| | J | | | | | | | |

**Other Documents**

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|---|---|---|
| BC | K | Jan, C.H., et al, *90NM Generation, 300mm Wafer Low k ILD/Cu Interconnect Technology*, 2003 IEEE Interconnect Technology Conference. |
| BC | L | U.S. Application No. 10/820,525 (Atty Docket No.: NOVLP091), entitled: METHODS FOR PRODUCING LOW-K CDO FILMS WITH LOW RESIDUAL STRESS, Wu et al. |
| | M | |

| Examiner /Bret Chen/ | Date Considered 06/11/2006 |
|---|---|

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (M dified) | Atty Docket No. | Application No.: |
|---|---|---|
| | NOVLP098 | 10/800,409 |
| **Inf rmation Disclo[illegible]** | Applicant: | |
| **Statement By Applicant** | Wu et al. | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | 03-11-2004 | 1762 |

**U.S. Patent Documents**

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|---|---|---|---|---|---|---|---|
| BC | A1 | 6,329,017 | 12.11.01 | Liu et al. | | | |
| | A2 | 6,383,466 | 05.07.02 | Domansky et al. | | | |
| | A3 | 6,365,266 | 04.02.02 | MacDougall et al. | | | |
| | A4 | 5,504,042 | 04.02.96 | Cho et al. | | | |
| | A5 | 5,858,457 | 01.12.96 | Brinker et al. | | | |
| | A6 | 6,270,846 | 08.07.01 | Brinker et al. | | | |
| | A7 | 6,387,453 | 05.14.02 | Brinker et al. | | | |
| | A8 | 5,789,027 | 08.04.98 | Watkins et al. | | | |
| | A9 | 6,391,932 B1 | 05.21.02 | Gore et al. | | | |
| | A10 | 5,700,844 | 12.23.97 | Hedrick et al. | | | |
| | A11 | 2003/0157248 A1 | 08.21.03 | Watkins et al. | | | |
| | A12 | 2002/0123240 A1 | 09.05.02 | Gallagher et al. | | | |
| | A13 | 6,596,654 | 07.22.03 | Bayman, et al. | | | |
| | A14 | 4,885,262 | 12.05.89 | Ting et al. | | | |
| | A15 | 5,686,054 | 11.11.97 | Barthel et al. | | | |
| | A16 | 5,851,715 | 12.22.98 | Barthel et al. | | | |
| | A17 | 6,140,252 | 10.31.00 | Cho et al. | | | |
| | A18 | 6,392,017 | 05.21.02 | Chandrashekar | | | |
| | A19 | 6,386,466 | 05.14.02 | Ozawa et al. | | | |
| | A20 | 4,357,451 | 11.02.02 | McDaniel | | | |
| | A21 | 6,479,374 | 11.12.02 | Ioka et al. | | | |
| | A22 | 6,548,113 | 04.15.03 | Birnbaum et al. | | | |
| | A23 | 2004/0099952 | 05.27.04 | Goodner et al. | | | |
| | A24 | 2004/0102031 | 05.27.04 | Kloster et al. | | | |
| | A25 | 2004/0185679 | 09.23.04 | Ott et al. | | | |
| | A26 | 2004/0096672 A1 | 05.20.04 | Lukas et al. | | | |
| | A27 | 6,444,715 | 09.2002 | Mukherjee et al. | | | |
| | A28 | 6,848,458 | 02.01.05 | Shrinivasan et al. | | | |
| | A29 | 6,805,801 | 10.19.04 | Humayun et al. | | | |
| | A30 | 6,391,932 | 05.21.02 | Gore et al. | | | |
| | A31 | 6,271,273 | 10.10.00 | You et al. | | | |
| | A32 | 6,420,441 | 10.10.99 | Allen et al. | | | |
| | A33 | 2002/0034626 | 03.21.02 | Liu et al. | | | |
| BC | A34 | 2002/0001973 | 01.03.02 | Wu et al. | | | |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (M dified) | Atty Docket No. | Application No.: |
|---|---|---|
| | NOVLP098 | 10/800,409 |
| **Information Disclosure** | Applicant: | |
| **Statement By Applicant** | Wu et al. | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | 03-11-2004 | 1762 |

**U.S. Patent Documents**

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|---|---|---|---|---|---|---|---|
| BC | A35 | 4,882,008 | 11.21.89 | Garza et al. | | | |
| | A36 | 6,329,062 | 12.11.01 | Gaynor | | | |
| | A37 | 6,268,276 | 07.31.01 | Chan et al. | | | |
| | A38 | 6,177,329 | 01.23.01 | Pang | | | |
| | A39 | 5,920,790 | 07.1999 | Wetzel et al. | | | |
| | A40 | 2003/0119307 | 06.2003 | Bekiaris et al. | | | |
| | A41 | 6,596,467 | 07.22.03 | Gallagher et al. | | | |
| | A42 | 6,667,147 | 12.23.03 | Gallagher et al. | | | |
| | A43 | 6,312,793 | 11.06.01 | Grill et al. | | | |
| | A44 | 6,576,345 | 06.10.03 | Cleemput et al. | | | |
| | A45 | 6,677,251 | 01.2004 | Lu et al. | | | |
| | A46 | 6,812,043 | 11.2004 | Bao et al. | | | |
| | A47 | 6,831,284 | 12.2004 | Demos et al. | | | |
| | A48 | 2002/0106500 | 08.2002 | Albano et al. | | | |
| | A49 | 2003/0064607 | 04.2003 | Leu et al. | | | |
| | A50 | 2004/0069410 | 04.2004 | Moghadam et al. | | | |
| | A51 | 6,756,085 | 06.29.04 | Waldfried et al. | | | |
| BC | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |

**Foreign Patent or Published Foreign Patent Application**

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation Yes | Translation No |
|---|---|---|---|---|---|---|---|---|
| BC | B1 | WO95/07543 | 03.16.95 | WIPO | | | X | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |

| Examiner | /Bret Chen/ | Date Considered | 06/11/2006 |
|---|---|---|---|

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (M dified)<br><br>Inf rmation Disclosure Statement By Applicant<br><br>(Use Several Sheets if Necessary) | Atty Docket No.<br>NOVLP098<br>Applicant:<br>Wu et al.<br>Filing Date<br>03-11-2004 | Application No.:<br>10/800,409<br><br><br><br>Group<br>1762 |
|---|---|---|

**Other Documents**

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|---|---|---|
| BC | C1 | Cho et al., "Plasma Treatments of Molecularly Templated Nanoporous Silica Films," Electrochemical and Solid-State Letters, 4 (4) G35-G38 (2001) |
| | C2 | Yung et al., "Spin-on Mesoporous Silica Films with Ultralow Dielectric Constants, Ordered Pore Structures, and Hydrophobic Surfaces," Adv. Mater. 2001, *13*, No. 14, 1099-1102 |
| | C3 | Schulberg et al., "System for Deposition of Mesoporous Materials," U.S. Patent Application No. 10/295,965, filed November 15, 2002, 64 Pages |
| | C4 | Watkins et al., "Mesoporous Materials and Methods," U.S. Patent Application No.10/301,013, filed November 21, 2002, 34 Pages |
| | C5 | Justin F. Gaynor, "In-Situ Treatment of Low-K Films With a Silylating Agent After Exposure To Oxidizing Environments," U.S. Patent Application No.10/056,926 filed January 24, 2002, 34 Pages |
| | C6 | Humayun et al., "Method for Forming Porous Films By Porogen Removel Combined Wtih In SITU Surface Modification", Novellus Corporation, Application No. 10/404,693, filed 3/31/03, pages 1-32. Atty. Docket No. NOVLP064/NVLS-0007 |
| | C7 | Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", Novellus Systems, Inc., Application No. 10/672,311, filed 9/26/03, pages 1-27. Atty. Docket No. NOVLP075/NVLS-000820 |
| | C8 | U.S. Patent Application No. 10/016,017, File Date: December 12, 2001 (Atty Dkt: NOVLP030) |
| | C9 | U.S. Patent Application No. 10/125,614, File Date: April 18, 2002 (Atty Dkt: NOVLP028) |
| | C10 | U.S. Patent Application No. 10/202,987, File Date: July 23, 2002 (Atty Dkt: NOVLP028X1) |
| | C11 | Tipton et al., "Method for Removal of Porogens From Porous Low-K Films Using Supercritical Fluids", Novellus Systems, Inc., Application No. 10/672,305, filed 9/26/03, pages 1-32. Atty. Docket No. NOVLP069/NVLS-000821 |
| | C12 | Gangpadhyay et al., "The First International Surface Cleaning Workshop," Northeastern University, November 11-14, 2002 |
| | C13 | Cho et al., "Method and Apparatus for UV Exposure of Low Dielectric Constant Materials for Porogen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 10/800,377, filed 3/11/04, pages 1-31. Atty. Docket No. NOVLP089/NVLS-2887 |
| BC | | |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (Modified)<br><br>**Inf rmation Disclosure Statement By Applicant**<br><br>(Use Several Sheets if Necessary) | Atty Docket No.<br>NOVLP098<br>Applicant:<br>Wu et al.<br>Filing Date<br>03-11-2004 | Application No.:<br>10/800,409<br><br><br><br>Group<br>1762 |
|---|---|---|

**Other Documents**

| | | | |
|---|---|---|---|
| BC | C14 | Wu et al., "Method and Apparatus of UV Exposure of Low Dielectric Constant Materials for Porogen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 10/807,680, filed 3/23/04, pages 1-34. Atty. Docket No. NOVLP097/NVLS-2906 |
| | C15 | Humayun et al., "Method For Forming Porous Films By Porogen Removal Combined With In Situ Modification", U.S. Patent No. 10/404,693, filed March 31, 2003, Office Action dated March 15, 2005 (Atty Dkt: NOVLP064) |
| | C16 | Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated September 7, 2004 (Atty Dkt: NOVLP075/NVLS-000820) |
| | C17 | Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated December 28, 2004 (Atty Dkt: NOVLP075/NVLS-000820) |
| | C18 | Tipton et al., "Method For Removal Of Porogens From Porous Low-K Films Using Supercritical Fluids", U.S. Patent No. 10/672,305, Office Action dated March 22, 2005 (Atty Dkt: NOVLP069). |
| | C19 | Bandyopadhyay et al., "Method to Improve Mechanical Strength of Low-K Dielectric Film Using Modulated UV Exposure", U.S. Patent Application No. 10/825,888, filed April 16, 2004 (Atty Dkt: NOVLP088US/NVLS-2882) |
| | C20 | R.D. Miller et al., "Phase-Separated Inorganic-Organic Hybrids for Microelectronic Applications," MRS Bulletin, October 1997, Pages 44-48 |
| | C21 | Jin et al., "Nanoporous Silica as an Ultralow-*k* Dielectric," MRS Bulletin, October 1997, Pages 39-42 |
| | C22 | Asoh et al., "Fabrication of Ideally Ordered Anodic Porous Alumina with 63 nm Hole Periodocity Using Sulfuric Acid," J. Vac. Sci. Technol. B 19(2), Mar/Apr 2001, Pages 569-572 |
| | C23 | Asoh et al., "Conditions for Fabrication of Ideally Ordered Anodic Porous Alumina Using Pretextured Al," Journal of the Electrochemica Society, 148 (4) B152-B156 (2001) Pages B152-B156 |
| | C24 | Holland et al., "Nonlithographic Technique for the Production of Large Area High Density Gridded Field Sources," J. Vac. Sci. Technol. B 17(2), Mar/Apr. 1999, Pages 580-582 |
| | C25 | Masuda et al. "Highly Ordered Nanochannel-Array Architecture in Anodic Alumina," App. Phys. Lett. 71(19), November 1997, Pages 2770-2772 |
| BC | C26 | Clube et al., "White Paper from Holotronic Technologies SA; downloaded from www.hdotronic.com/whitepaper/fine-patt.pdf on March 12, 2002 |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| F rm 1449 (M dified) | Atty Docket No. | Application No.: |
|---|---|---|
| | NOVLP098 | 10/800,409 |
| **Inf rmati n Disclosure** | Applicant: | |
| **Statement By Applicant** | Wu et al. | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | 03-11-2004 | 1762 |

**Other Documents**

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|---|---|---|
| BC | C29 | Meli et al., "Self-Assembled Masks for the Transfer of Nanometer-Scale Patterns into Surfaces: Characterization by AFM and LFM", Nano Letters, Vol. 2, No. 2, 2002, 131-135 |
| | C30 | "Shipley Claims Porous Low K Dielectric Breakthrough," Press Release March 17, 2003. |
| | C31 | Jeffrey M. Calvert and Michael K. Gallagher, Semiconductor International, 26 (12), 56 (2003). |
| | C32 | Van Bavel et al., Future Fab International, 16, (2004). |
| | C33 | Caluwaerts et al, "Post Patterning Meso Porosity Creation: A Potential Solution For Pore Sealing," IITC 2003. |
| | C34 | Peter Singer, "New Materials and Designs to Improve Transistor Performance", April 1, 2004, Semiconductor International. |
| | C35 | Ghani et al, "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors", IEEE, © 2003. |
| | C36 | Bhadri N. Varadarajan, "Tensile Silicon Nitride – P1264 NESL", C & F Study, August 21, 2003. |
| | C37 | Varadarajan, et al., "Strained Transistor Architecture and Method", Novellus Systems, Inc., Appln No. 10/923,259, filed August 20,2004, pages 1-24. [Atty Docket No. NOVLP108/NVLS-2933]. |
| | C38 | Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, filed June 2, 2004, (Atty Dkt: NOVLP099) |
| | C39 | Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Office Action dated March 2, 2005, (Atty Dkt: NOVLP099) |
| | C40 | Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Final Office Action dated June 13, 2005, (Atty Dkt: NOVLP099) |
| | C41 | Wang et al., "Plasma Detemplating And Silanol Capping Of Porous Dielectric Films", U.S. Application No. 10/785,235, filed February 23, 2004 (Atty Dkt: NOVLP085) |
| | C42 | Varadarajan et al., "Tensile Dielectric Films Using UV Curing", U.S. Application No. 10/972,084, filed October 22, 2004 (Atty Dkt: NOVLP122) |
| BC | C43 | Fox et al., "Method For Improving Mechanical Properties Of Low Dielectric Constant Materials", U.S. Application No. 10/849,568, filed May 18, 2004 (Atty Dkt: NOVLP083) |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (Modified)<br><br>**Informati n Discl sure Statement By Applicant**<br><br>(Use Several Sheets if Necessary) | Atty Docket No.<br>NOVLP098<br>Applicant:<br>Wu et al.<br>Filing Date<br>03-11-2004 | Application No.:<br>10/800,409<br><br><br>Group<br>1762 |
|---|---|---|

**Other Documents**

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|---|---|---|
| BC | C44 | Fox et al., "Methods For Producing Low-Stress Carbon-Doped Oxide Films With Improved Integration Properties", U.S. Application No. 10/987,208, filed November 12, 2004 (Atty Dkt: NOVLP104) |
| | C45 | Van Den Hoek et al., "VLSI Fabrication Processes For Introducing Pores Into Dielectric Materials," U.S. Application No. 11/050,621, filed January 31, 2005 (Atty Dkt: NOVLP100) |
| | C46 | Draeger et al., "Creation Of Porosity In Low-K Films By Photo-Disassociation Of Imbedded Nanoparticles," U.S. Application No. 11/146,456, filed June 6, 2005 (Atty Dkt: NOVLP100X1) |
| | C47 | Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 10/927,777, filed August 27, 2004 (Atty Dkt: NOVLP106) |
| | C48 | Wu et al., "Methods For Improving Integration Performance Of Low Stress CDO Films", U.S. Application No. 10/941,502, filed September 14, 2004 (Atty Dkt: NOVLP107) |
| | C49 | Cho et al., "Methods of Improving Porogen Removal and Film Mechanical Strength in Producing Ultra Low-K Carbon Doped Oxide Films Using Radical Photopolymerization", U.S. Application No. 10/982,654, filed November 5, 2004 (Atty Dkt: NOVLP115) |
| | C50 | Wu et al., U.S. Application No. 10/789,103 (Atty Docket No.: NOVLP094), entitled: Methods For Producing Low-K CDO Films With Low Residual Stress |
| BC | | |
| | | |
| | | |
| | | |
| | | |
| | | |
| | | |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (Modified) | Atty Docket No. | Application No.: |
|---|---|---|
| | NOVLP098 | 10/800,409 |
| **Information Disclosure Statement By Applicant** | Applicant: Wu et al. | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | 03-11-2004 | 1762 |

**U.S. Patent Documents**

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|---|---|---|---|---|---|---|---|
| BC | A1 | 6,500,770 B1 | 12.2002 | Cheng et al. | | | |
| / BC | A2 | 2002/0192980 A1 | 12.2002 | Hogle et al. | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |

**Foreign Patent or Published Foreign Patent Application**

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation Yes | Translation No |
|---|---|---|---|---|---|---|---|---|
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |

**Other Documents**

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|---|---|---|
| BC | C1 | U.S. Office Action mailed July 13, 2005, from U.S Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820]. |
| BC | C2 | U.S. Office Action mailed July 27, 2005, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875]. |
| | | |
| | | |
| | | |
| | | |
| | | |
| | | |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (M dified) | Atty Docket No. | Application No.: |
|---|---|---|
| | NOVLP098 | 10/800,409 |
| **Information Disclosure Statement By Applicant** | Applicant: | |
| | Wu et al. | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | 03-11-2004 | 1762 |

**U.S. Patent Documents**

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|---|---|---|---|---|---|---|---|
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |

**Foreign Patent or Published Foreign Patent Application**

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation | |
|---|---|---|---|---|---|---|---|---|
| | | | | | | | Yes | No |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |

**Other Documents**

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|---|---|---|
| BC | C1 | U.S. Office Action mailed August 24, 2005, from U.S Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794]. |
| BC | C2 | U.S. Office Action mailed September 1, 2005, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821]. |
| | | |
| | | |
| | | |
| | | |
| | | |
| | | |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form 1449 (Modified) | Atty Docket No. | Application No.: |
|---|---|---|
| **Information Disclosure Statement By Applicant** | NOVLP098 | 10/800,409 |
| | Applicant: | |
| | Wu et al. | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | 03-11-2004 | 1762 |

**U.S. Patent Documents**

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|---|---|---|---|---|---|---|---|
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |

**Foreign Patent or Published Foreign Patent Application**

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation Yes | Translation No |
|---|---|---|---|---|---|---|---|---|
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |

**Other Documents**

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
|---|---|---|
| BC | C1 | Cho et al., "Method for Porogen Removal and Mechanical Strength Enhancement of Low-K Carbon Doped Silicon Oxide Using Low Thermal Budget Microwave Curing", U.S. Application No. 11/280,113, filed November 15, 2005 (Atty Dkt: NOVLP145/NVLS-3106) |
| | | |
| | | |
| | | |
| | | |
| | | |
| | | |
| | | |

| Examiner | Date Considered |
|---|---|
| /Bret Chen/ | 06/11/2006 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.